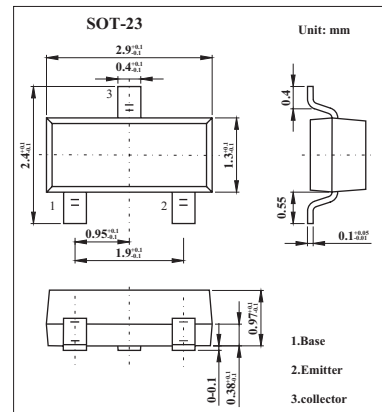


NPN Switching Transistors

BSR13,BSR14

■ Features

- High current (max. 800 mA).
- Low voltage (max. 40 V).

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	BSR13	BSR14	Unit
Collector-base voltage	V_{CB0}	60	75	V
Collector-emitter voltage	V_{CE0}	30	40	V
Emitter-base voltage	V_{EB0}	5	6	V
Collector current	I_C	800		mA
Peak collector current	I_{CM}	800		mA
Peak base current	I_{BM}	200		mA
Total power dissipation	P_{tot}	250		mW
Storage temperature	T_{stg}	-65 to +150		$^\circ\text{C}$
Junction temperature	T_j	150		$^\circ\text{C}$
Operating ambient temperature	R_{amb}	-65 to +150		$^\circ\text{C}$
Thermal resistance from junction to ambient *	$R_{th\ j-a}$	500		K/W

* Transistor mounted on an FR4 printed-circuit board.

BSR13,BSR14

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	BSR13	$I_E = 0; V_{CB} = 50\text{ V}$			30	nA
		$I_E = 0; V_{CB} = 50\text{ V}; T_J = 150\text{ }^\circ\text{C}$			10	μA
	BSR14	$I_E = 0; V_{CB} = 60\text{ V}$			10	nA
		$I_E = 0; V_{CB} = 60\text{ V}; T_J = 150\text{ }^\circ\text{C}$			10	μA
Emitter cutoff current	BSR13	$I_C = 0; V_{EB} = 5\text{ V}$			30	nA
	BSR14				10	nA
DC current gain *		$I_C = 0.1\text{ mA}; V_{CE} = 10\text{ V};$ $I_C = 1\text{ mA}; V_{CE} = 10\text{ V};$ $I_C = 10\text{ mA}; V_{CE} = 10\text{ V};$ $I_C = 150\text{ mA}; V_{CE} = 10\text{ V}$ $I_C = 150\text{ mA}; V_{CE} = 1\text{ V};$	35			
			50			
			75			
			100		300	
			50			
DC current gain *	BSR13	$I_C = 500\text{ mA}; V_{CE} = 10\text{ V};$	30			
	BSR14		40			
collector-emitter saturation voltage	BSR13	$I_C = 150\text{ mA}; I_B = 15\text{ mA}$			400	mV
	BSR14				300	mV
collector-emitter saturation voltage	BSR13	$I_C = 500\text{ mA}; I_B = 50\text{ mA}$			1.6	V
	BSR14				1	V
base-emitter saturation voltage	BSR13	$I_C = 150\text{ mA}; I_B = 15\text{ mA}$			1.3	V
	BSR14		0.6		1.2	V
base-emitter saturation voltage	BSR13	$I_C = 500\text{ mA}; I_B = 50\text{ mA}$			2.6	V
	BSR14				2	V
Collector capacitance	C_c	$I_E = I_C = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$		8		pF
Transition frequency	BSR13	$I_C = 20\text{ mA}; V_{CE} = 20\text{ V}; f = 100\text{ MHz}$	250			MHz
	BSR14		300			MHz
Turn-on time	t_{on}	$I_{Con} = 150\text{ mA}; I_{Bon} = 15\text{ mA};$ $I_{Boff} = -15\text{ mA}$			35	ns
Delay time	t_d				15	ns
Rise time	t_r				20	ns
Turn-off time	t_{off}				250	ns
Storage time	t_s				200	ns
Fall time	t_f				60	ns

* Pulse test: $t_p \leq 300\text{ }\mu\text{s}; d \leq 0.02$.

■ hFE Classification

TYPE	BSR13	BSR14
Marking	U7	U8